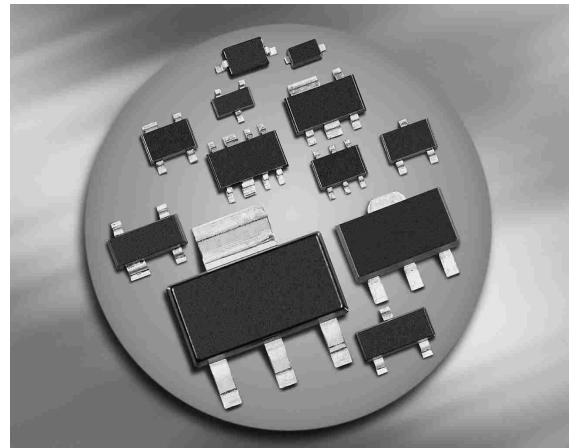
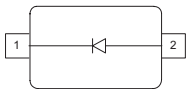


Silicon Variable Capacitance Diode

- For UHF-TV-tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure



BB545
BB565/-02V



Type	Package	Configuration	L_s (nH)	Marking
BB545	SOD323	single	1.8	white U
BB565	SCD80	single	0.6	CC
BB 565-02V	SC79	single	0.6	C

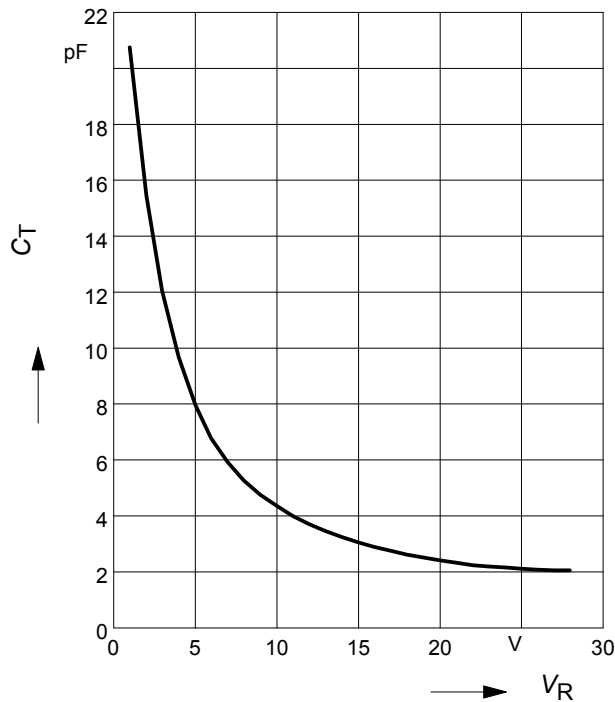
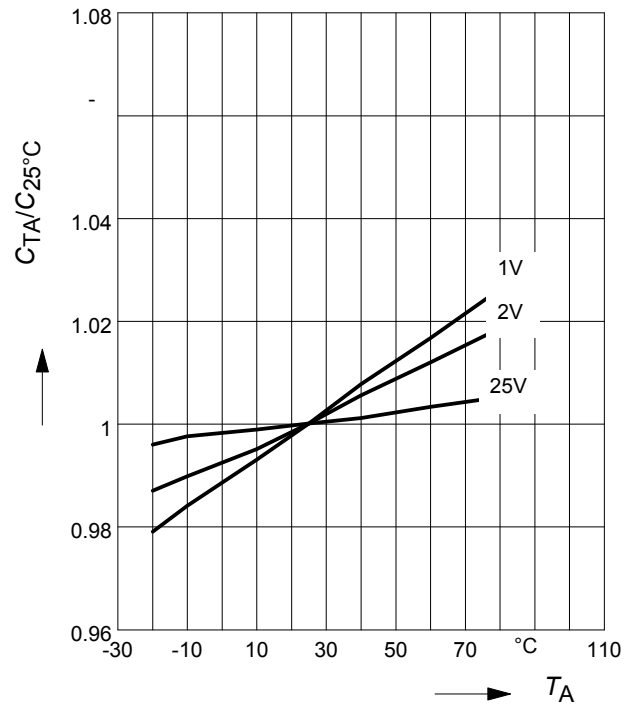
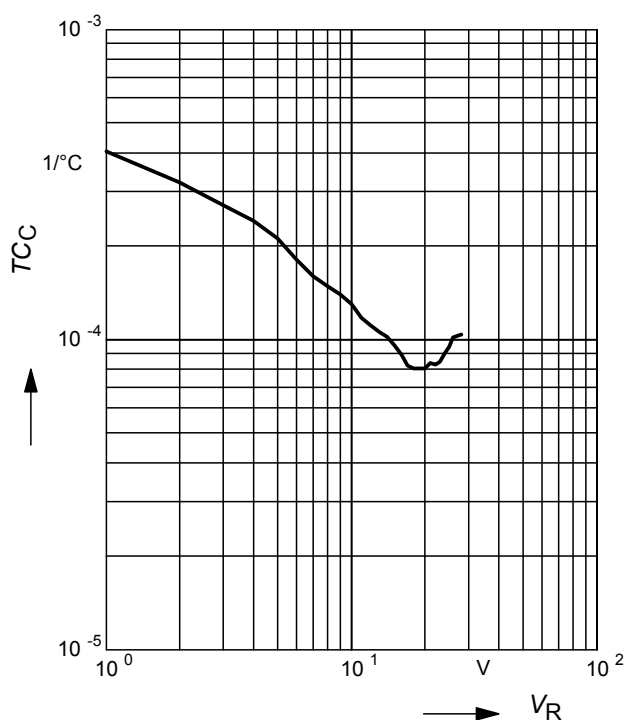
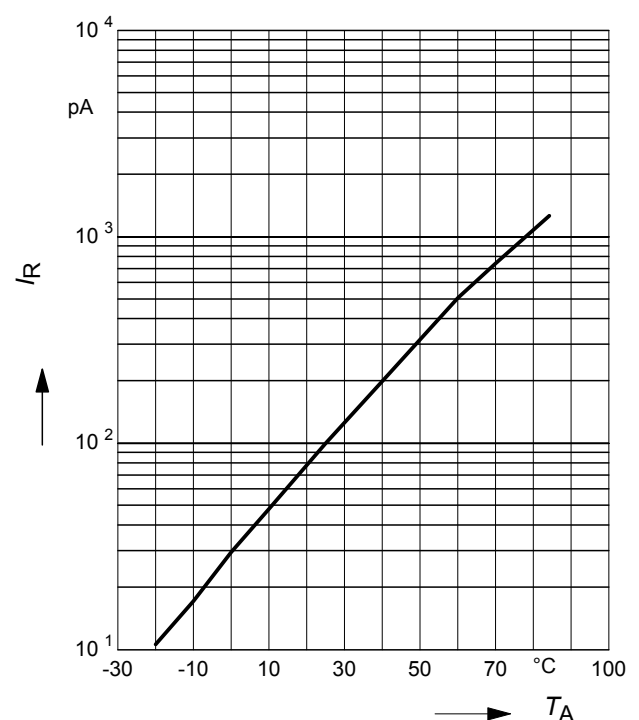
Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage $R \geq 5\text{k}\Omega$	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_R				nA
$V_R = 30\text{ V}$		-	-	10	
$V_R = 30\text{ V}, T_A = 85\text{ }^{\circ}\text{C}$		-	-	200	
AC Characteristics					
Diode capacitance	C_T				pF
$V_R = 1\text{ V}, f = 1\text{ MHz}$		18.5	20	21.5	
$V_R = 2\text{ V}, f = 1\text{ MHz}$		13.2	14.8	16.4	
$V_R = 25\text{ V}, f = 1\text{ MHz}$		1.85	2.07	2.28	
$V_R = 28\text{ V}, f = 1\text{ MHz}$		1.8	2	2.2	
Capacitance ratio	C_{T1}/C_{T28}	9	10	11	-
$V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$					
Capacitance ratio	C_{T2}/C_{T25}	6.3	7.2	8.1	
$V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$					
Capacitance matching ¹⁾	$\Delta C_T/C_T$				%
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, \textbf{7}$ diodes sequence, BB545		-	-	2.5	
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, \textbf{4}$ diodes sequence, BB565/ -02V		-	0.5	1.5	
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, \textbf{7}$ diodes sequence, BB565/ -02V		-	0.7	2	
Series resistance	r_S	-	0.6	-	Ω
$V_R = 3\text{ V}, f = 470\text{ MHz}$					

¹For details please refer to Application Note 047

Diode capacitance $C_T = f(V_R)$
 $f = 1\text{MHz}$

Normalized diode capacitance
 $C_{(T_A)}/C_{(25^\circ\text{C})} = f(T_A); f = 1\text{MHz}$
 $V_R = \text{Parameter}$

Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$

Reverse current $I_R = f(T_A)$
 $V_R = 28\text{V}$


Reverse current $I_R = f(V_R)$

T_A = Parameter

